

# MT3400

## N-Channel Power MOSFET

### General Description

This N-Channel Logic Level MOSFET is produced using Mos-tech's Semiconductor's advanced PowerTrech process that has been especially tailored to minimize on-state resistance and yet maintain superior switching performance.

These devices are well suited for low voltage and battery powered applications where low in-line power loss and fast switching are required.

### Features

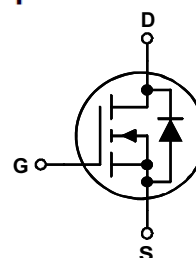
- 4.0 A, 30 V.  $R_{DS(ON)} = 0.025\Omega @ V_{GS} = 10\text{ V}$   
 $R_{DS(ON)} = 0.042\Omega @ V_{GS} = 4.5\text{ V}$
- Very fast switching speed.
- Low gate charge (5nC typical)
- High performance version of industry standard SOT-23 package. Identical pin out to SOT-23 with 30% higher power handling capability.



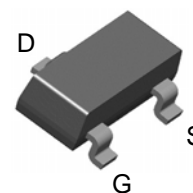
**MT Semiconductor®**

<http://www.mtsemi.com>

### Simplified Schematic



### MARKING DIAGRAM & PIN ASSIGNMENT



**SOT-23-3L**

### Absolute Maximum Ratings ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Ratings	Units
$V_{DSS}$	Drain-Source Voltage	30	V
$V_{GSS}$	Gate-Source Voltage	$\pm 12$	V
$I_D$	Maximum Drain Current – Continuous (Note 1a)	4.0	A
		10	
$P_D$	Maximum Power Dissipation (Note 1a) (Note 1b)	1.25	W
		0.76	
$T_J, T_{STG}$	Operating and Storage Temperature Range	$-55$ to $+150$	$^\circ\text{C}$

### Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	100	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1)	75	$^\circ\text{C/W}$

### Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
MT3400	MT3400	7"	8mm	3000 units

**Electrical Characteristics**  $T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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**Off Characteristics**

$BV_{DSS}$	Drain–Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$ , Referenced to $25^\circ\text{C}$		21		mV/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 24\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
		$T_J = -55^\circ\text{C}$			10	$\mu\text{A}$
$I_{GSS}$	Gate–Body Leakage	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$			$\pm 100$	nA

**On Characteristics** (Note 2)

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		0.9	1.6	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$ , Referenced to $25^\circ\text{C}$		–4		mV/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain–Source On–Resistance	$V_{GS} = 10\text{ V}, I_D = 2.7\text{ A}$ $V_{GS} = 4.5\text{ V}, I_D = 2.4\text{ A}$ $V_{GS} = 10\text{ V}, I_D = 2.7\text{ A}, T_J = 125^\circ\text{C}$		0.020 0.030 0.053	0.025 0.042 0.075	$\Omega$
$I_{D(on)}$	On–State Drain Current	$V_{GS} = 10\text{ V}, V_{DS} = 5\text{ V}$	10			A
$g_{FS}$	Forward Transconductance	$V_{DS} = 5\text{ V}, I_D = 2.7\text{ A}$		4.6		S

**Dynamic Characteristics**

$C_{iss}$	Input Capacitance	$V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V},$		600		pF
$C_{oss}$	Output Capacitance	$f = 1.0\text{ MHz}$		55		pF
$C_{rss}$	Reverse Transfer Capacitance			41		pF
$R_G$	Gate Resistance	$f = 1.0\text{ MHz}$		1.8		$\Omega$

**Switching Characteristics** (Note 2)

$t_{d(on)}$	Turn–On Delay Time	$V_{DD} = 15\text{ V}, I_D = 1\text{ A},$		2.5		ns
$t_r$	Turn–On Rise Time	$V_{GS} = 10\text{ V}, R_{GEN} = 6\text{ }\Omega$		2.5		ns
$t_{d(off)}$	Turn–Off Delay Time			20		ns
$t_f$	Turn–Off Fall Time			4		ns
$Q_g$	Total Gate Charge	$V_{DS} = 15\text{ V}, I_D = 2.7\text{ A},$		4		nC
$Q_{gs}$	Gate–Source Charge	$V_{GS} = 5\text{ V}$		0.6		nC
$Q_{gd}$	Gate–Drain Charge			1.5		nC

**Drain–Source Diode Characteristics and Maximum Ratings**

$I_S$	Maximum Continuous Drain–Source Diode Forward Current			0.42		A
$V_{SD}$	Drain–Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 0.42\text{ A}$ (Note 2)		0.7	1.2	V
$t_{rr}$	Diode Reverse Recovery Time	$IF = 2.7\text{ A}, diF/dt = 100\text{ A}/\mu\text{s}$		12	20	ns
$Q_{rr}$	Diode Reverse Recovery Charge			3	5	nC

**Notes:**

1.  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.



a)  $250^\circ\text{C/W}$  when mounted on a  $0.02\text{ in}^2$  pad of 2 oz. copper.



b)  $270^\circ\text{C/W}$  when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width  $\leq 300\text{ }\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$

## Typical Characteristics

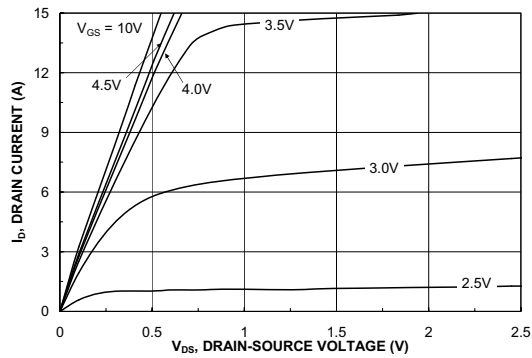


Figure 1. On-Region Characteristics.

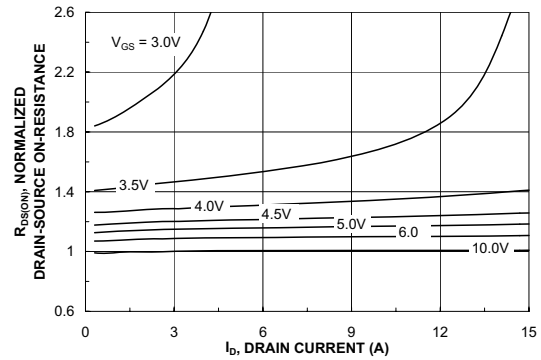


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

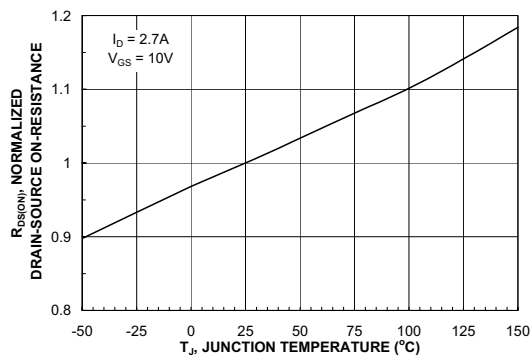


Figure 3. On-Resistance Variation with Temperature.

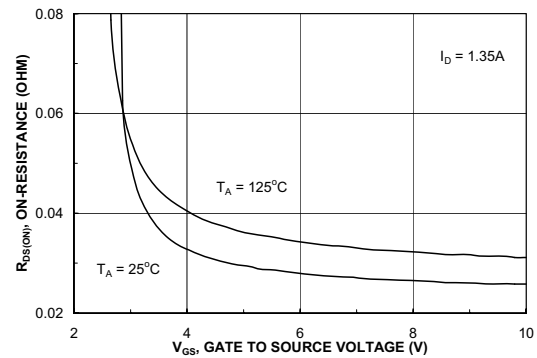


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

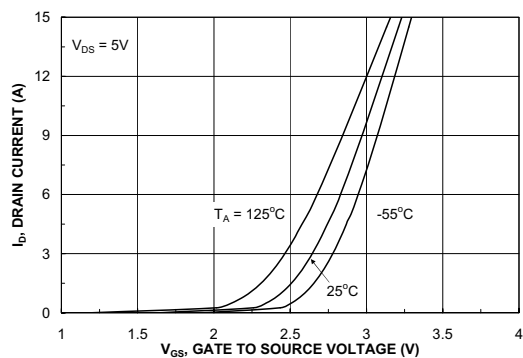


Figure 5. Transfer Characteristics.

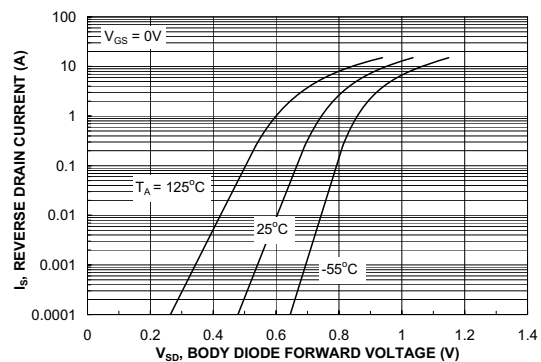


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

## Typical Characteristics

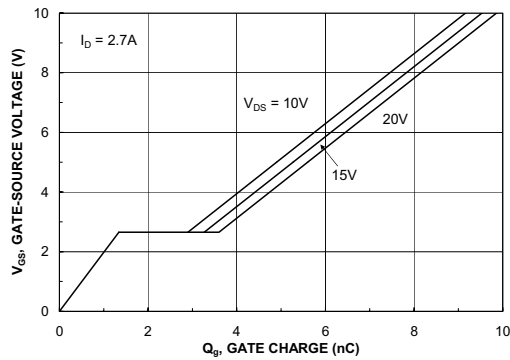


Figure 7. Gate Charge Characteristics.

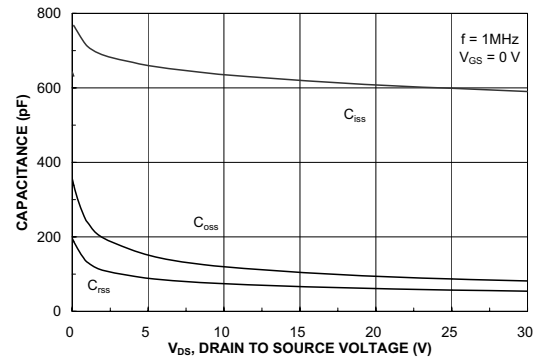


Figure 8. Capacitance Characteristics.

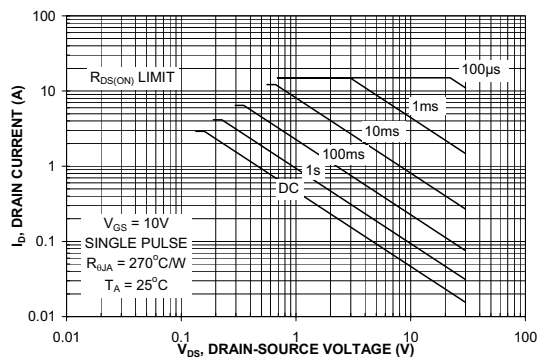


Figure 9. Maximum Safe Operating Area.

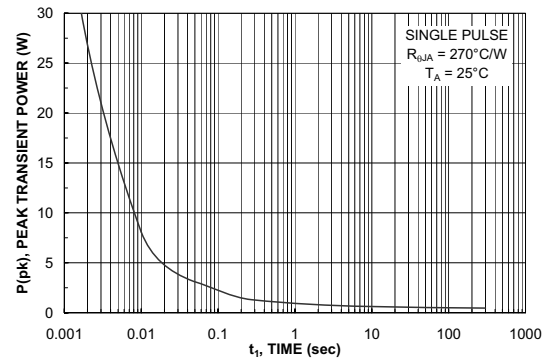


Figure 10. Single Pulse Maximum Power Dissipation.

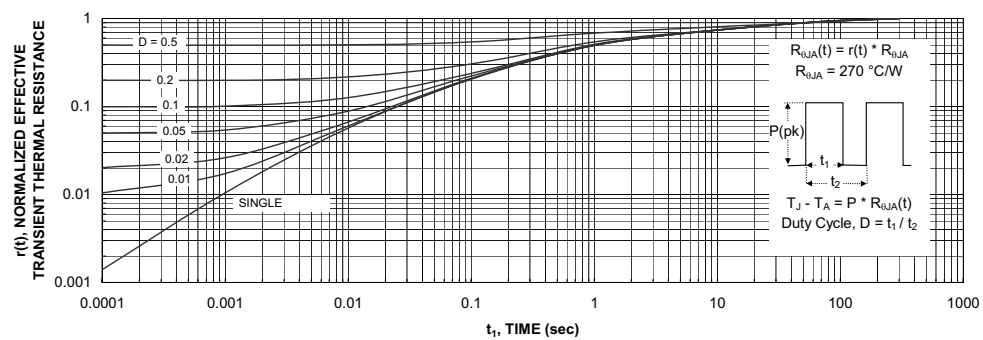


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1b.  
Transient thermal response will change depending on the circuit board design.

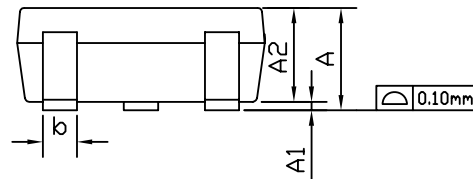
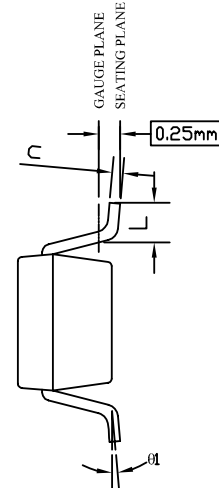
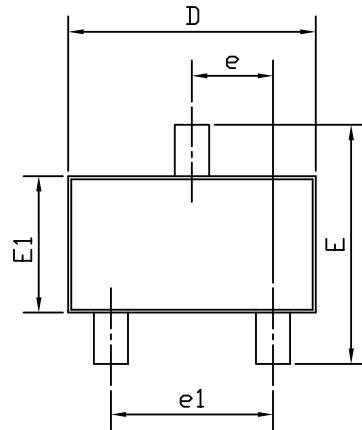
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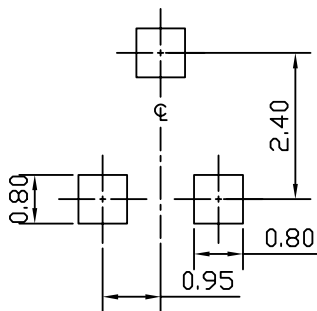
Version

L

## SOT23 PACKAGE OUTLINE



## RECOMMENDED LAND PATTERN



UNIT: mm

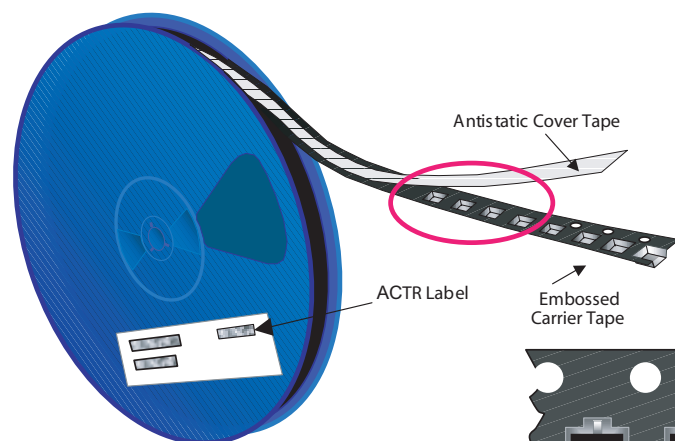
SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.85	—	1.25	0.033	—	0.049
A1	0.00	—	0.13	0.000	—	0.005
A2	0.70	1.00	1.15	0.028	0.039	0.045
b	0.30	0.40	0.50	0.012	0.016	0.020
c	0.08	0.13	0.20	0.003	0.005	0.008
D	2.80	2.90	3.10	0.110	0.114	0.122
E	2.60	2.80	3.00	0.102	0.110	0.118
E1	1.40	1.60	1.80	0.055	0.063	0.071
e	0.95 BSC			0.037 BSC		
e1	1.90 BSC			0.075 BSC		
L	0.30	—	0.60	0.012	—	0.024
θ1	0°	5°	8°	0°	5°	8°

## NOTE

1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH OR GATE BURRS.  
MOLD FLASH AT THE NON-LEAD SIDES SHOULD BE LESS THAN 5 MILS EACH.
2. TOLERANCE  $\pm 0.100$  mm (4 mil) UNLESS OTHERWISE SPECIFIED.
3. DIMENSION L IS MEASURED IN GAUGE PLANE.
4. CONTROLLING DIMENSION IS MILLIMETER. CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.
5. ALL DIMENSIONS ARE IN MILLIMETERS.

## SOT-23 Std Tape and Reel Data

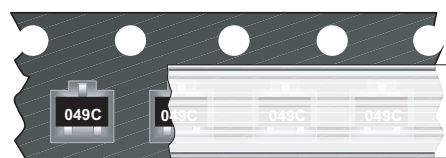
### SOT23-3L Packaging Configuration: Figure 1.0



#### Packaging Description:

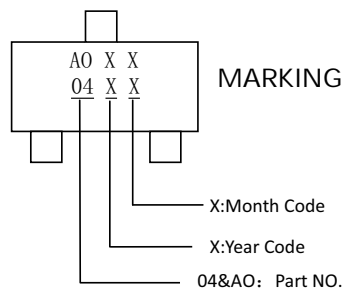
SOT23-3L parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 3,000 units per 7" or 177mm diameter reel. The reels are dark blue in color and is made of polystyrene plastic (anti-static coated). Other option comes in 10,000 units per 13" or 330cm diameter reel. This and some other options are described in the Packaging Information table.

These full reels are individually labeled and placed inside a standard immediate box made of recyclable corrugated brown paper with a Fairchild logo printing. One box contains five reels maximum. And these immediate boxes are placed inside a labeled shipping box which comes in different sizes depending on the number of parts shipped.



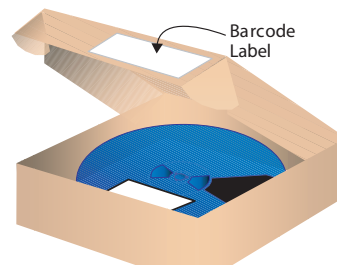
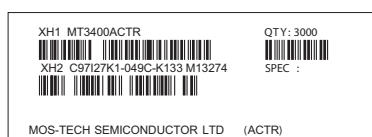
#### SOT23-3L Unit Orientation

SOT23-3L Packaging Information		
Packaging Option	Standard (no flow code)	D87Z
Packaging type	TNR	TNR
Qty per Reel/Tube/Bag	3,000	10,000
Reel Size	7" Dia	13"
Box Dimension (mm)	193x183x80	355x333x40
Max qty per Box	15,000	30,000
Weight per unit (gm)	0.0082	0.0082
Weight per Reel (kg)	0.1175	0.4006
Note/Comments		



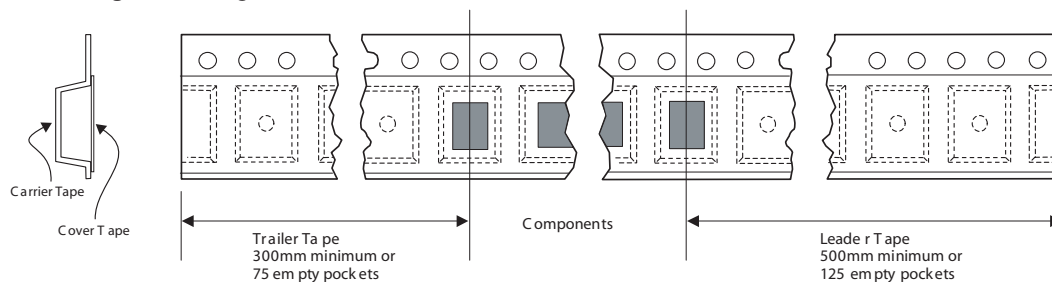
#### MARKING DIAGRAM

#### Barcode Label sample



193mm x 183mm x 80mm  
Pizza Box for Standard Option

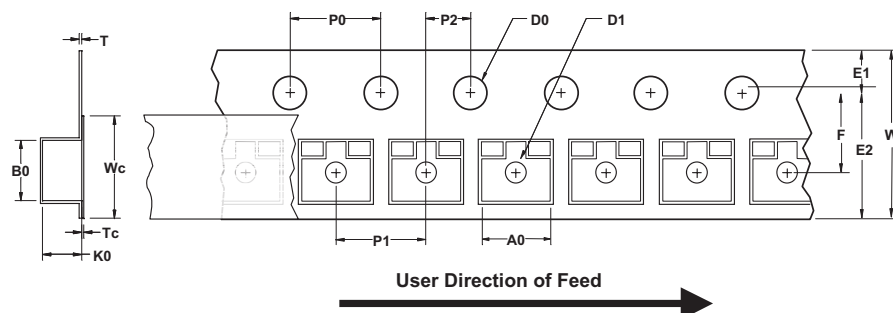
### SOT23-3L Tape Leader and Trailer Configuration: Figure 2.0



## SOT-23 Std Tape and Reel Data, continued

### SOT23-3L Embossed Carrier Tape

Configuration: Figure 3.0



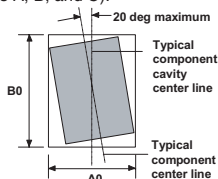
Dimensions are in millimeter

Pkg type	A0	B0	W	D0	D1	E1	E2	F	P1	P0	K0	T	Wc	Tc
SOT-23 (8mm)	3.15 +/-0.10	2.77 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.30 +/-0.10	0.228 +/-0.013	5.2 +/-0.3	0.06 +/-0.02

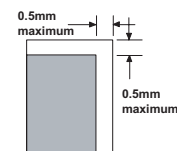
Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)  
Component Rotation

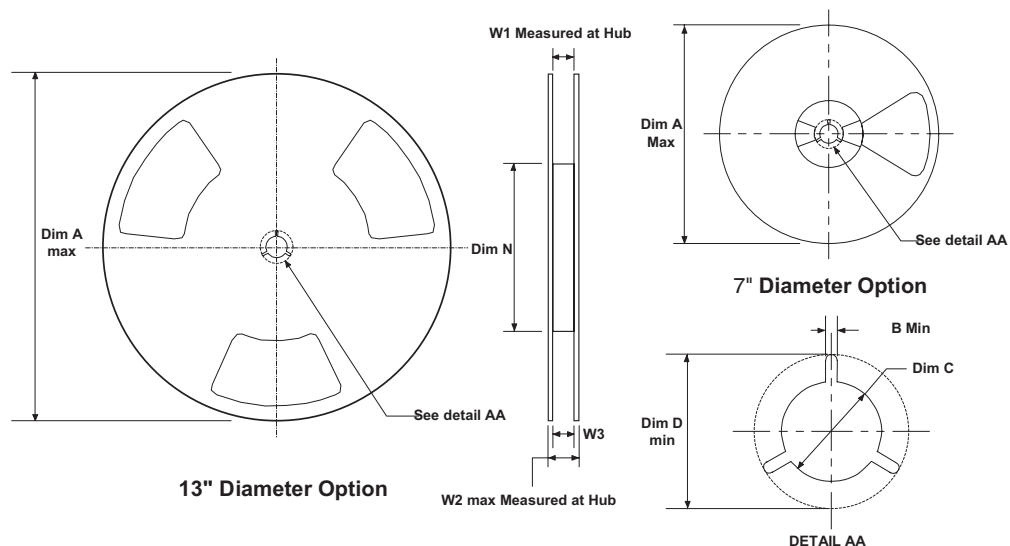


Sketch B (Top View)  
Component Rotation



Sketch C (Top View)  
Component lateral movement

### SOT23-3L Reel Configuration: Figure 4.0



Dimensions are in inches and millimeters

Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9

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  - 1) 生命维持装置。
  - 2) 植埋于人体使用的装置。
  - 3) 用于治疗(切除患部、给药等)的装置。
  - 4) 其他直接影响到人的生命的装置。
9. 在使用本资料所记载的产品时, 对于最大额定值、工作电源电压的范围、放热特性、安装条件及其他条件请在本公司规定的保证范围内使用。如果超出了本公司规定的保证范围使用时, 对于由此而造成的故障和出现的事, 本公司将不承担任何责任。
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11. 如果把本资料所记载的产品从其载体设备上卸下, 有可能造成婴儿误吞的危险。顾客在将本公司产品安装到顾客的设备上时, 请顾客自行负责将本公司产品设置为不容易剥落的安全设计。如果从顾客的设备上剥落而造成事故时, 本公司将不承担任何责任。
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### Keep safety first in your circuit designs!

1. MOS-TECH Semiconductor Corp. puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage.  
Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.